

IRF3708S-VB Datasheet

N-Channel 20-V (D-S), 175°C MOSFET



RoHS
COMPLIANT
HALOGEN
FREE

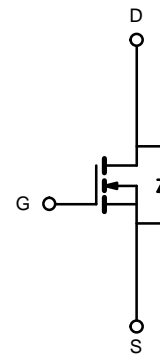
PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^a
20	0.006 @ $V_{GS} = 4.5$ V	85
	0.009 @ $V_{GS} = 2.5$ V	85

FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU

APPLICATIONS

- OR-ing
- Server
- DC/DC



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	20	V	
Gate-Source Voltage	V_{GS}	± 12		
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	85 ^a	A
		$T_C = 100^\circ\text{C}$	75	
Pulsed Drain Current	I_{DM}	240		
Avalanche Current	I_{AR}	30		
Repetitive Avalanche Energy ^b	E_{AR}	45	mJ	
Power Dissipation	P_D	120 ^a	W	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient	R_{thJA}	PCB Mount (TO-263) ^c	40	$^\circ\text{C/W}$
		Free Air (TO-220AB)	62.5	
Junction-to-Case	R_{thJC}	1.25		

Notes:

- See SOA curve for voltage derating.
- Duty cycle $\leq 1\%$.
- When mounted on 1" square PCB (FR-4 material).

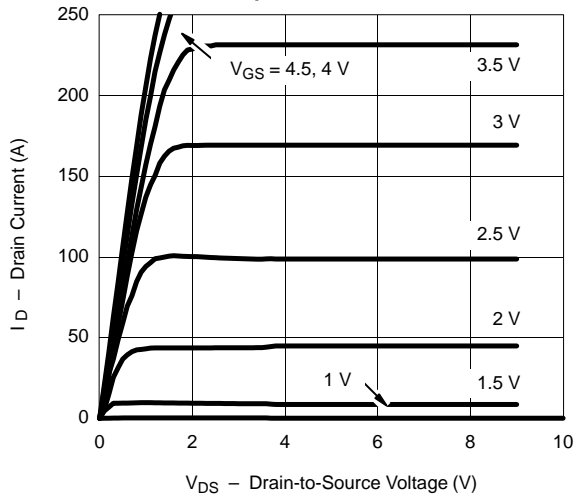
MOSFET SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _{DS} = 250 μA	0.6			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 175 °C			150	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 4.5 V	120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 30 A		0.006		Ω
		V _{GS} = 4.5 V, I _D = 30 A, T _J = 125 °C		0.009		
		V _{GS} = 4.5 V, I _D = 30 A, T _J = 175 °C		0.0111		
		V _{GS} = 2.5 V, I _D = 20 A		0.009		
Forward Transconductance ^a	g _{fs}	V _{DS} = 5 V, I _D = 30 A	20			S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 20 V, f = 1 MHz		6600		pF
Output Capacitance	C _{oss}			1150		
Reversen Transfer Capacitance	C _{riss}			600		
Total Gate Charge ^c	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 85 A		65	130	nC
Gate-Source Charge ^c	Q _{gs}			13		
Gate-Drain Charge ^c	Q _{gd}			14		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 10 V, R _L = 0.12 Ω I _D = 85 A, V _{GEN} = 4.5 V, R _G = 2.5 Ω		25	40	ns
Rise Time ^c	t _r			120	180	
Turn-Off Delay Time ^c	t _{d(off)}			80	120	
Fall Time ^c	t _f			100	150	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)^b						
Pulsed Current	I _{SM}				240	A
Forward Voltage ^a	V _{SD}	I _F = 100 A, V _{GS} = 0 V		1.2	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		45	100	ns

Notes:

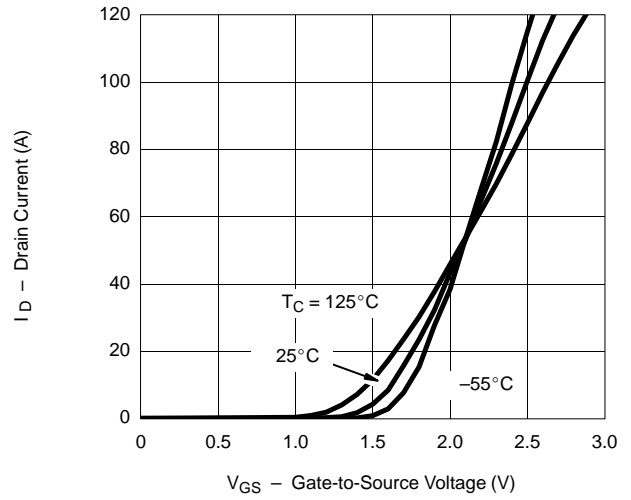
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

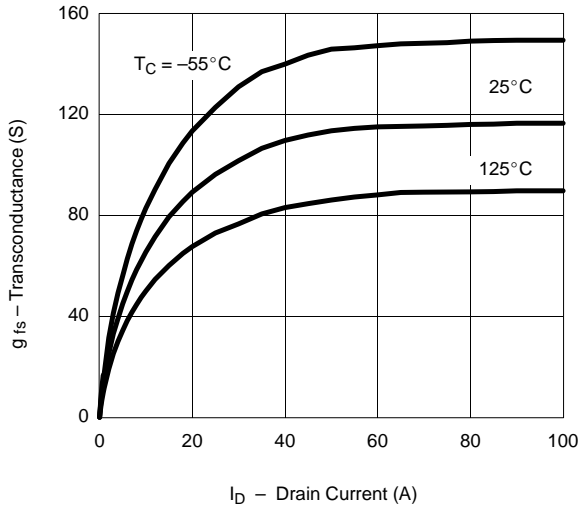
Output Characteristics



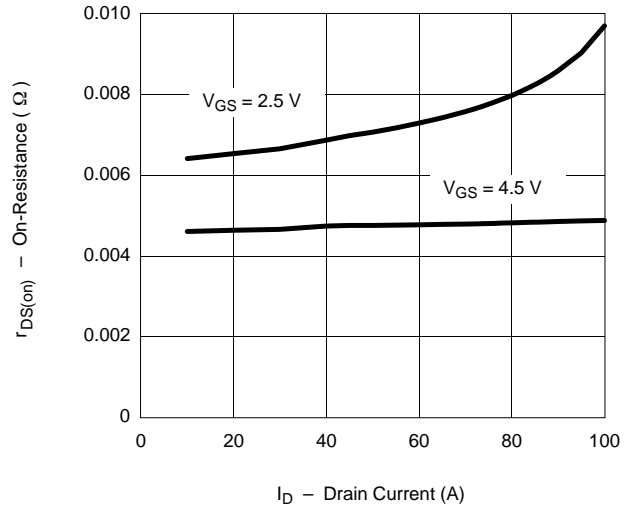
Transfer Characteristics



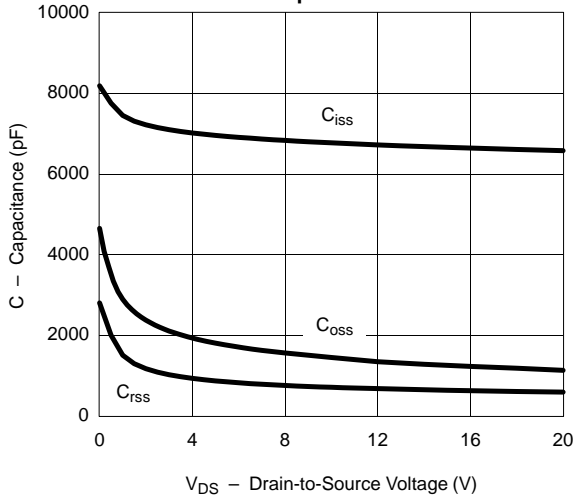
Transconductance



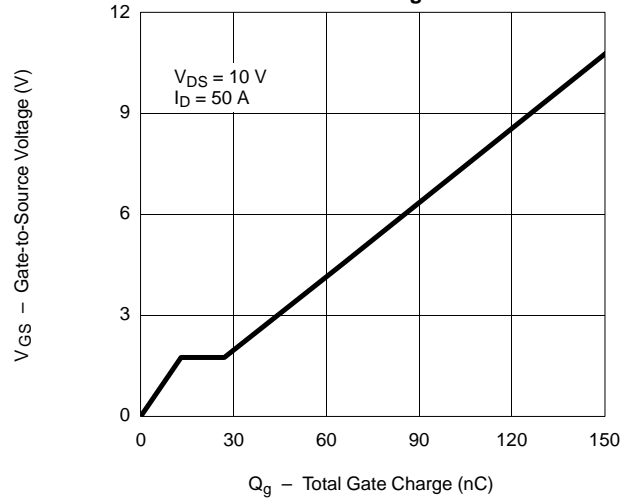
On-Resistance vs. Drain Current



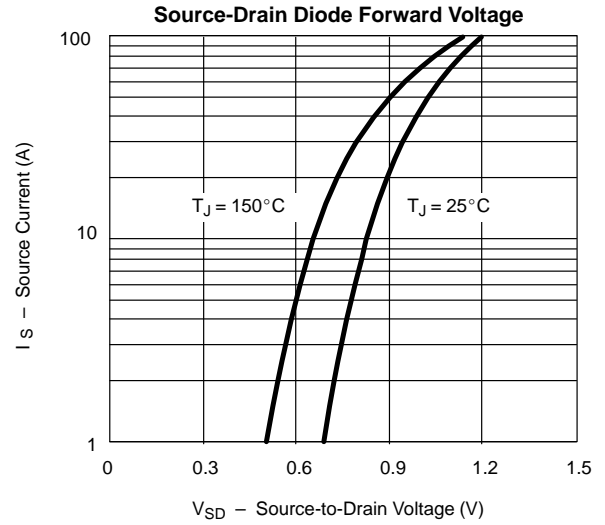
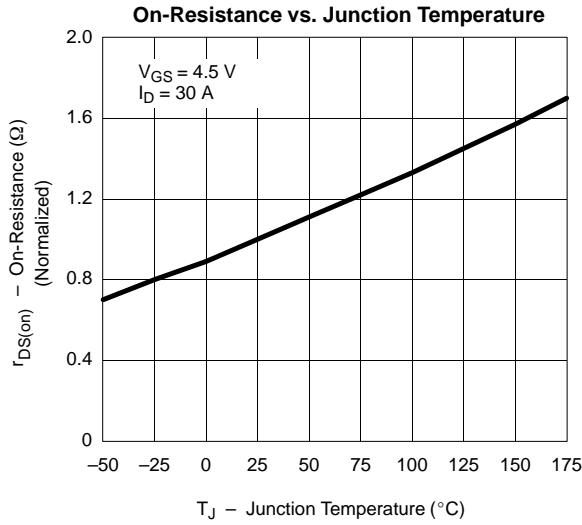
Capacitance



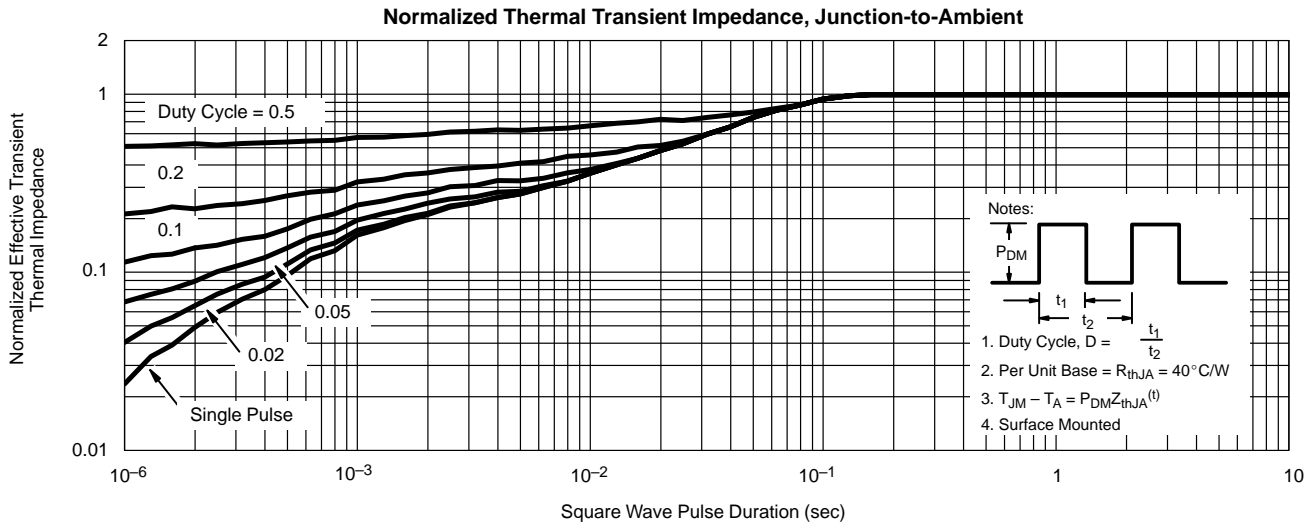
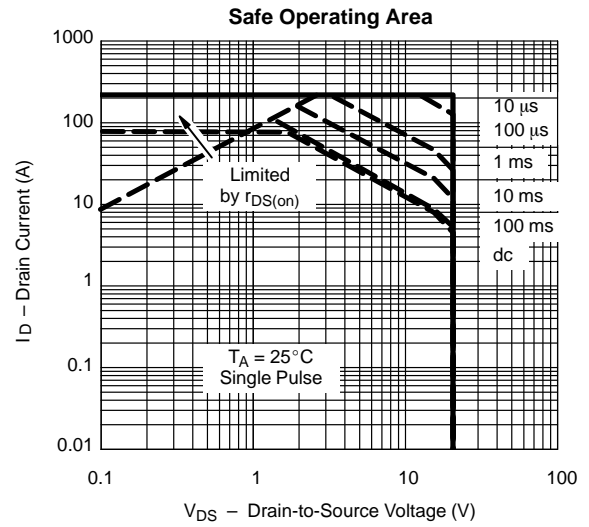
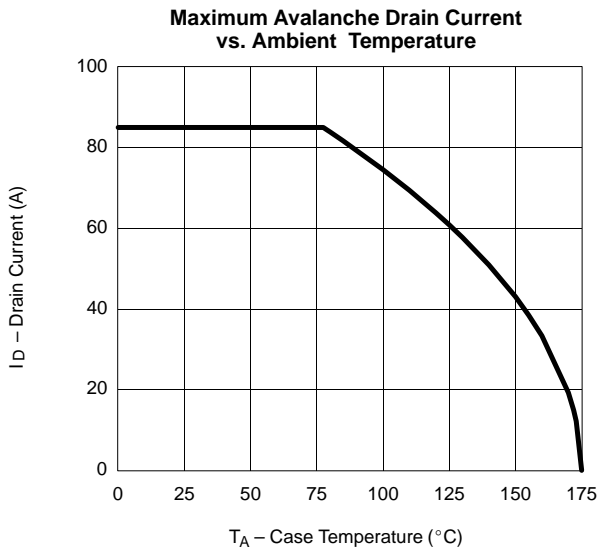
Gate Charge



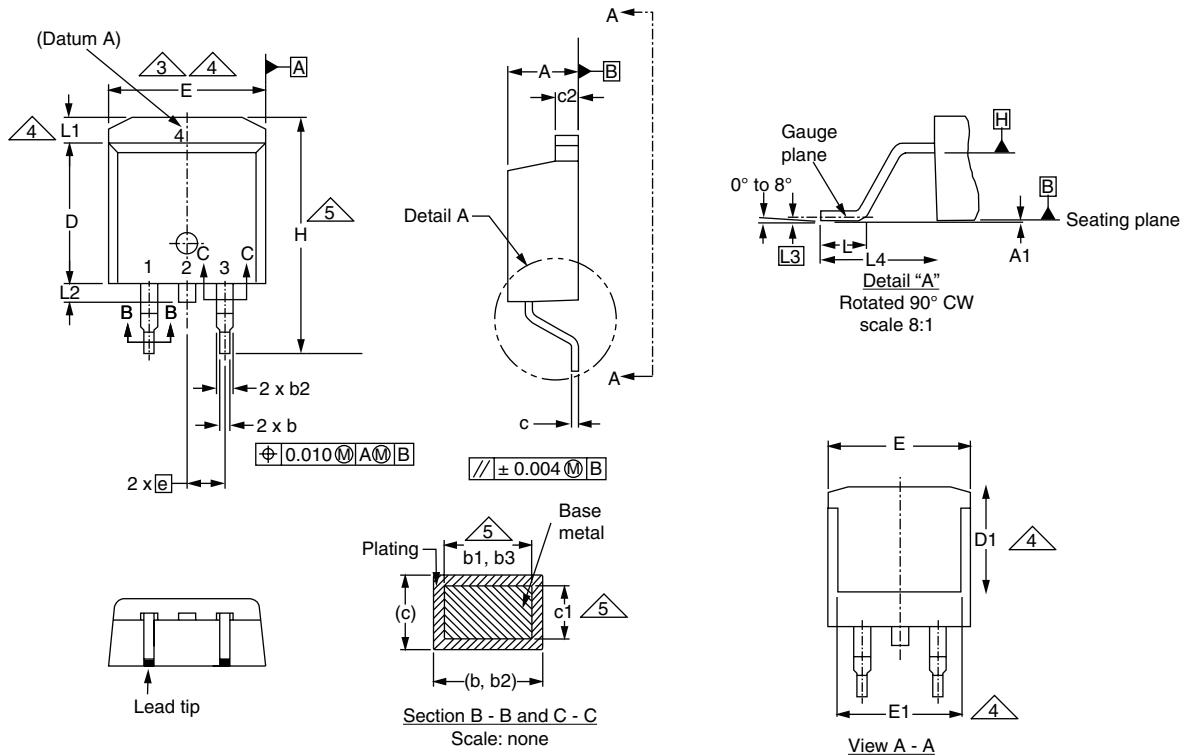
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



THERMAL RATINGS



TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

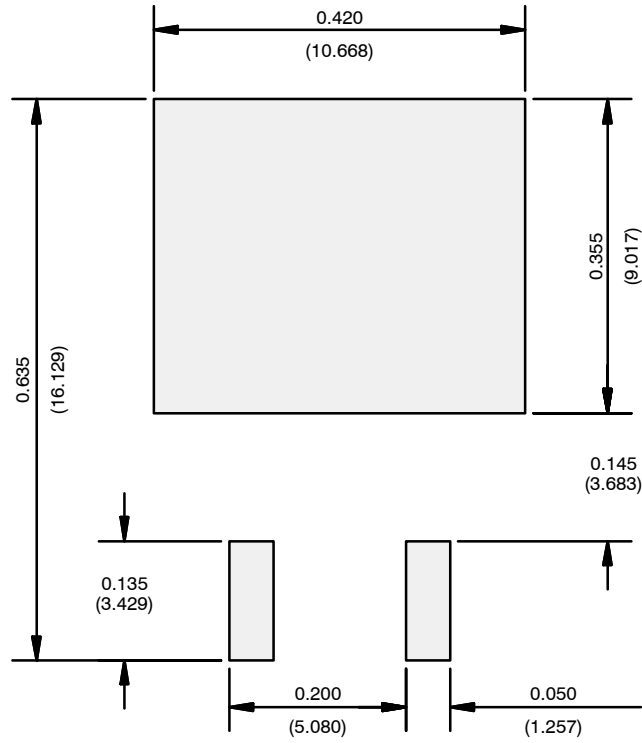
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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